

December 2011

FOD814 Series, FOD817 Series 4-Pin High Operating Temperature Phototransistor Optocouplers

Features

- AC input response (FOD814 only)
- Applicable to Pb-free IR reflow soldering
- Compact 4-pin package
- Current transfer ratio in selected groups:

FOD814: 20–300% FOD814A: 50–150% FOD817: 50–600% FOD817A: 80–160%

FOD817B: 130–260% FOD817C: 200–400% FOD817D: 300–600%

- C-UL, UL and VDE approved
- High input-output isolation voltage of 5000Vrms
- Minimum BV_{CFO} of 70V guaranteed
- Higher operating temperatures (versus H11AXXX counterparts)

Applications

FOD814 Series

- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface

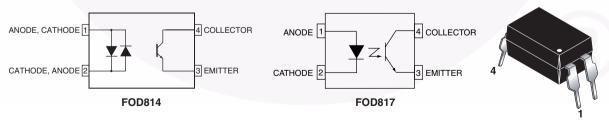
FOD817 Series

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

Description

The FOD814 consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a silicon phototransistor output in a 4-pin dual in-line package. The FOD817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.

Functional Block Diagram



Absolute Maximum Ratings (T_A = 25°C Unless otherwise specified.)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

		Va	alue	Units
Symbol	Parameter	FOD814	FOD817	
TOTAL DEVIC	DE .			1
T _{STG}	Storage Temperature	-55 t	o +150	°C
T _{OPR}	Operating Temperature	-55 to +105	-55 to +110	°C
T _{SOL}	Lead Solder Temperature	260 fc	or 10 sec	°C
T _J	Junction Temperature	125	Max.	°C
$\theta_{\sf JC}$	Junction-to-Case Thermal Resistance	2	210	°C/W
P _{TOT}	Total Power Dissipation	2	200	
EMITTER				
l _F	Continuous Forward Current	±50	50	mA
V_{R}	Reverse Voltage		6	
P _D	Power Dissipation		70	
	Derate above 100°C		1.7	
DETECTOR				
V_{CEO}	Collector-Emitter Voltage		70	
V _{ECO}	Emitter-Collector Voltage		6	
Ic	Continuous Collector Current		50	mA
P _C	Collector Power Dissipation		150	mW
	Derate above 90°C		2.9	mW/°C

Electrical Characteristics (T_A = 25°C Unless otherwise specified.)

Individual Component Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER							
V _F	Forward Voltage	FOD814	$I_F = \pm 20 \text{mA}$		1.2	1.4	V
		FOD817	I _F = 20mA		1.2	1.4	
I _R	Reverse Leakage Current	FOD817	V _R = 4.0V			10	μΑ
C _t	Terminal Capacitance	FOD814	V = 0, f = 1kHz		50	250	pF
		FOD817	V = 0, f = 1kHz		30	250	
DETECTOR	?			•			
I _{CEO}	Collector Dark Current	FOD814	$V_{CE} = 20V, I_F = 0$			100	nA
		FOD817	$V_{CE} = 20V, I_F = 0$			100	
BV _{CEO}	Collector-Emitter Breakdown	FOD814	$I_C = 0.1 \text{mA}, I_F = 0$	70			V
	Voltage	FOD817	$I_C = 0.1 \text{mA}, I_F = 0$	70			
BV _{ECO}	Emitter-Collector Breakdown	FOD814	$I_E = 10 \mu A, I_F = 0$	6			V
	Voltage	FOD817	$I_E = 10\mu A, I_F = 0$	6			

DC Transfer Characteristics

	DC						
Symbol	Characteristic	Device	Test Conditions	Min.	Тур.*	Max.	Unit
CTR	Current Transfer	FOD814	$I_F = \pm 1 \text{mA}, V_{CE} = 5V^{(1)}$	20		300	%
	Ratio	FOD814A		50		150	
		FOD817	$I_F = 5mA, V_{CE} = 5V^{(1)}$	50		600	
		FOD817A		80		160	
		FOD817B		130		260	
		FOD817C		200		400	
		FOD817D		300		600	
V _{CE (sat)}	Collector-Emitter	FOD814	$I_F = \pm 20$ mA, $I_C = 1$ mA		0.1	0.2	V
	Saturation Voltage	FOD817	$I_F = 20$ mA, $I_C = 1$ mA		0.1	0.2	

AC Transfer Characteristics

Symbol	AC Characteristic	Device	Test Conditions	Min.	Тур.*	Max.	Unit
f _C	Cut-Off Frequency	FOD814	V_{CE} = 5V, I_{C} = 2mA, R_{L} = 100 Ω , -3dB	15	80		kHz
t _r	Response Time (Rise)	FOD814, FOD817	$V_{CE} = 2 \text{ V}, I_{C} = 2\text{mA}, R_{L} = 100\Omega^{(2)}$		4	18	μs
t _f	Response Time (Fall)	FOD814, FOD817			3	18	μs

^{*}Typical values at T_A = 25°C

$\textbf{Electrical Characteristics} \; (T_{A} = 25 ^{\circ}\text{C Unless otherwise specified.}) \; (\text{Continued})$

Isolation Characteristics

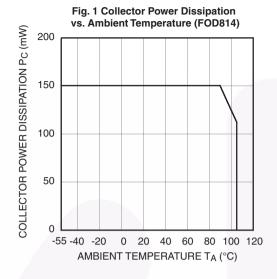
Symbol	Characteristic	Device	Test Conditions	Min.	Typ.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage ⁽³⁾	FOD814, FOD817	$\begin{aligned} f &= 60 Hz, \ t = 1 \ min, \\ I_{I-O} &\leq 2 \mu A \end{aligned}$	5000			Vac(rms)
R _{ISO}	Isolation Resistance	FOD814, FOD817	V _{I-O} = 500VDC	5x10 ¹⁰	1x10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	FOD814, FOD817	V _{I-O} = 0, f = 1 MHz		0.6	1.0	pf

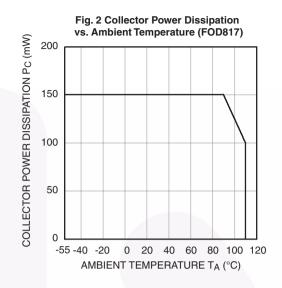
^{*}Typical values at $T_A = 25$ °C

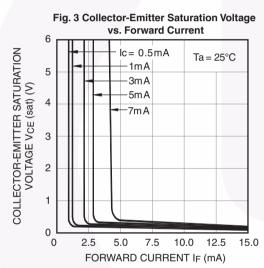
Notes:

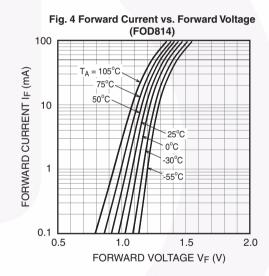
- 1. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- 2. For test circuit setup and waveforms, refer to page 7.
- 3. For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

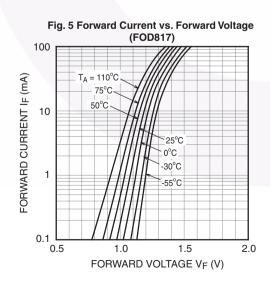
Typical Electrical/Optical Characteristics ($T_A = 25$ °C Unless otherwise specified.)

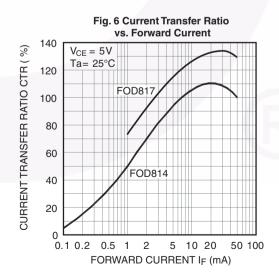












$\textbf{Typical Electrical/Optical Characteristics} \ (\texttt{Continued}) \ (\texttt{T}_{\texttt{A}} = 25^{\circ}\texttt{C} \ \texttt{Unless otherwise specified.})$

Fig. 7 Collector Current vs. Collector-Emitter Voltage (FOD814)

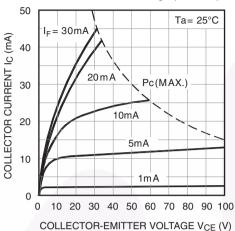


Fig. 8 Collector Current vs.
Collector-Emitter Voltage (FOD817)

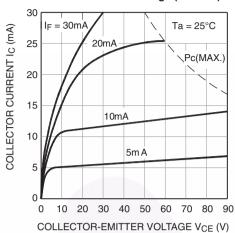


Fig. 9 Relative Current Transfer Ratio vs. Ambient Temperature

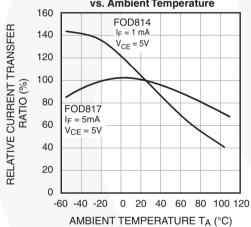


Fig. 10 Collector-Emitter Saturation Voltage vs. Ambient Temperature

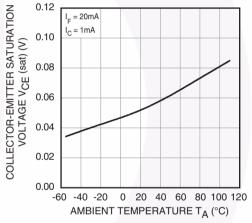


Fig. 11 LED Power Dissipation vs. Ambient Temperature (FOD814)

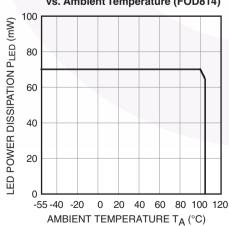
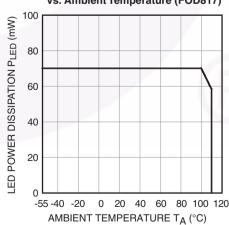


Fig. 12 LED Power Dissipation vs. Ambient Temperature (FOD817)



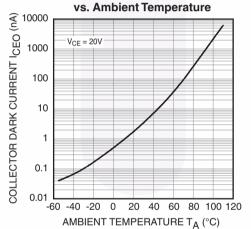
Typical Electrical/Optical Characteristics (Continued) (T_A = 25°C Unless otherwise specified.)

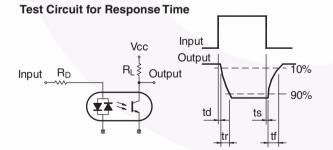
Fig. 13 Response Time vs. Load Resistance 100 $V_{CE} = 2V$ 50 Ic= 2mA Ta= 25°C 20 RESPONSE TIME (µs) 10 5 td 2 0.5 0.2 0.1 0.1 0.2 0.5 1 10

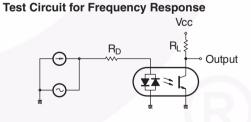
LOAD RESISTANCE R_I $(k\Omega)$

Fig. 14 Frequency Response V_{CE}= 2V Ic = 2mA $Ta = 25^{\circ}C$ VOLTAGE GAIN Ay (dB) R_L=10kΩ 100Ω -10 -20 0.5 0.2 152 10 1000 FREQUENCY f (kHz)

Fig. 15 Collector Dark Current vs. Ambient Temperature V_{CE} = 20V -40 -20 0 20 40 60 80 100 120 AMBIENT TEMPERATURE TA (°C)





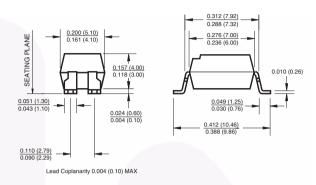


Package Dimensions

Through Hole

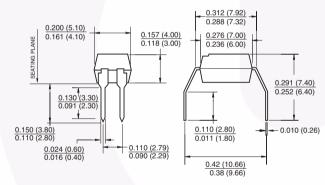
0.312 (7.92) 0.288 (7.32) 0.276 (7.00) 0.161 (4.10) 0.157 (4.00) 0.130 (3.30) 0.091 (2.30) 0.010 (0.26) 0.016 (0.40) 0.016 (0.40)

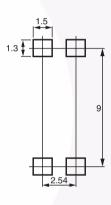
Surface Mount



Surface Mount (Footprint Dimensions)

0.4" Lead Spacing





Note:

All dimensions are in inches (millimeters)

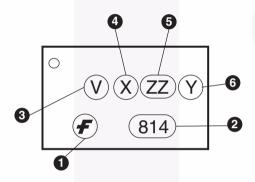
Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

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Ordering Information

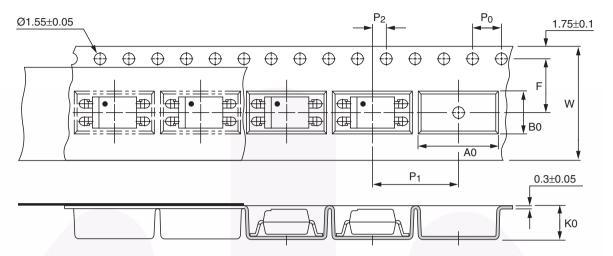
Option	Part Number Example	Description
S	FOD814S	Surface Mount Lead Bend
SD	FOD814SD	Surface Mount; Tape and reel
300	FOD814300	VDE Approved
300W	FOD814300W	VDE Approved, 0.4" Lead Spacing
3S	FOD8143S	VDE Approved, Surface Mount
3SD	FOD8143SD	VDE Approved, Surface Mount, Tape & Reel

Marking Information



Definiti	ons
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code
5	Two digit work week ranging from '01' to '53'
6	Assembly package code Y = Manufactured in Thailand YA = Manufactured in China

Carrier Tape Specifications

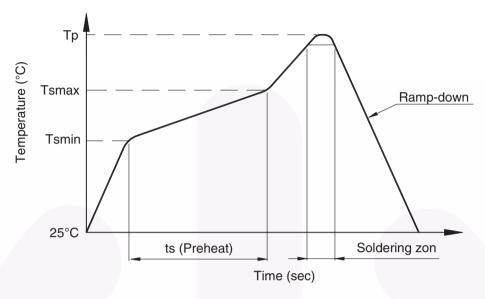


Note:

All dimensions are in millimeters.

Symbol	Description	Dimensions in mm (inches)
W	Tape wide	16 ± 0.3 (.63)
P ₀	Pitch of sprocket holes	4 ± 0.1 (.15)
F P ₂	Distance of compartment	7.5 ± 0.1 (.295) 2 ± 0.1 (.079)
P ₁	Distance of compartment to compartment	12 ± 0.1 (.472)
A0	Compartment	10.45 ± 0.1 (.411)
B0		5.30 ± 0.1 (.209)
K0		4.25 ± 0.1 (.167)

Lead Free Recommended IR Reflow Condition



Profile Feature	Pb-Sn solder assembly	Lead Free assembly
Preheat condition (Tsmin-Tsmax / ts)	100°C ~ 150°C 60 ~ 120 sec	150°C ~ 200°C 60 ~120 sec
Melt soldering zone	183°C 60 ~ 120 sec	217°C 30 ~ 90 sec
Peak temperature (Tp)	240 +0/-5°C	260 +0/-5°C
Ramp-down rate	6°C/sec max.	6°C/sec max.

Recommended Wave Soldering condition

Profile Feature	For all solder assembly
Peak temperature (Tp)	Max 260°C for 10 sec





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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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Rev. 154